

Supply Voltage	V_{CC}	-0.5 to 6.5	V
DC Input Diode Current $V_I = -0.5\text{ V}$ $V_I = V_{CC} + 0.5\text{ V}$	I_{IK}	-20 +20	mA
DC Input Voltage	V_I	-0.5 to $V_{CC} + 0.5$	V
DC Output Diode Current $V_O = -0.5\text{ V}$ $V_O = V_{CC} + 0.5\text{ V}$	I_{OK}	-20 +20	mA
DC Output Voltage	V_O	-0.5 to $V_{CC} + 0.5$	V
DC Output Source or Sink Current	I_O	± 50	mA
DC V_{CC} or Ground Current per Output Pin	I_{CC} or I_{GND}	± 50	mA
Storage Temperature	T_{STG}	-65 to +150	$^{\circ}\text{C}$

			°		- ° °			
V_{IH}	Minimum High Level Input Voltage	3.0	1.5	2.1	2.1	V	$V_{OUT} = 0.1\text{ V}$ or $V_{CC} - 0.1\text{ V}$	
		4.5	2.25	3.15	3.15			
		5.5	2.75	3.85	3.85			
V_{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.9	0.9	V	$V_{OUT} = 0.1\text{ V}$ or $V_{CC} - 0.1\text{ V}$	
		4.5	2.25	1.35	1.35			
		5.5	2.75	1.65	1.65			
V_{OH}	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9	V	$I_{OUT} = -50\text{ }\mu\text{A}$	
		4.5	4.49	4.4	4.4			
		5.5	5.49	5.4	5.4			
		3.0	-	2.56	2.46	V	$V_{IN} = V_{IL}$ or V_{IH} $I_{OH} = -12\text{ mA}$ $I_{OH} = -24\text{ mA}$ $I_{OH} = -24\text{ mA}$ (Note 1)	
		4.5	-	3.86	3.76			
		5.5	-	4.86	4.76			
V_{OL}	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1	V	$I_{OUT} = 50\text{ }\mu\text{A}$	
		4.5	0.001	0.1	0.1			
		5.5	0.001	0.1	0.1			
		3.0	-	0.36	0.44	V	$V_{IN} = V_{IL}$ or V_{IH} $I_{OL} = 12\text{ mA}$ $I_{OL} = 24\text{ mA}$ $I_{OL} = 24\text{ mA}$ (Note 1)	
		4.5	-	0.36	0.44			
		5.5	-	0.36	0.44			
I_{IN} (Note 3)	Maximum Input Leakage Current	5.5	-	± 0.1	± 1.0	μA	$V_I = V_{CC}, \text{ GND}$	
I_{OZ}	Maximum 3-State Current	5.5	-	± 0.25	± 2.5	μA	$V_I (\text{OE}) = V_{IL}, V_{IH}$ $V_I = V_{CC}, \text{ GND}$ $V_O = V_{CC}, \text{ GND}$	
I_{OLD}	Minimum Dynamic Output Current (Note 2)	5.5	-	-	75	mA	$V_{OLD} = 1.65\text{ V Max}$	
I_{OHD}		5.5	-	-	-75	mA	$V_{OHD} = 3.85\text{ V Min}$	
I_{CC} (Note 3)	Maximum Quiescent Supply Current	5.5	-	8.0	80	μA	$V_{IN} = V_{CC}$ or GND	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

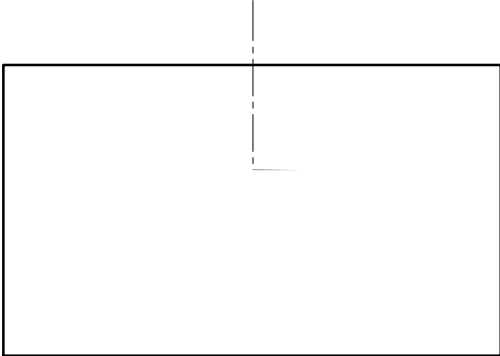
1. All outputs loaded; thresholds on input associated with output under test.
2. Maximum test duration 2.0 ms, one output loaded at a time.
3. I

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SOIC-20, 300 mils
CASE 751BJ
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